

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 12007-0074	SERIAL NO. 10/580,653
LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i>		APPLICANT Wolfgang STOLZ et al.	FILING DATE 03/30/2007
		GROUP ART UNIT 2826	

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES NO PART.

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

1.	C. SETIAGUNG et al., "Very Low Threshold Current Density of 1.3 μ m-range GaInNAsSb/GaNAs 5QWs Lasers", The Furukawa Electric Co., Ltd., Yokohama R&D Laboratories, © 2002, IEEE, pgs. 39-40
2.	E. GOUARDES et al., "GaInAs-GaInNAs-GaInAs Intermediate Layer Structure for Long Wavelength Lasers", <i>IEEE PHOTONICS TECHNOLOGY LETTERS</i> , vol. 14, No. 7, July 2002, pgs. 896-898
3.	M. KAWAGUCHI et al., "Photoluminescence and Lasing Characteristics of 1.3 μ m GaInNAs/GaAsP/GaAs Strain-compensated Quantum Wells", <i>Compound Semiconductors 2003</i> , International Symposium, August 25-27, 2003, pgs. 72-73

EXAMINER	/Kevin Quinto/	DATE CONSIDERED	07/15/2010
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.